## MSKSEMI















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# Broduct data sheet



SOD-523



## **BAT46X** SCHOTTKY BARRIER DIODE

#### **FEATURES**

- High breakdown voltage
- Low turn-on voltage
- Guard ring construction for transient protection

#### Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage		100	V
Working peak reverse voltage	$V_{RWM}$	V	
Forward continuous current	I <sub>F</sub>	150	mA
Repetitive peak forward current (Note 1) @ tp < 1.0s, Duty Cycle < 50%	I <sub>FRM</sub>	350	mA
Non-repetitive Peak Forward surge current @ t = 8.3ms	I <sub>FSM</sub>	750	mA
Power dissipation	P <sub>D</sub>	150	mW
Thermal resistance junction to ambient air	$R_{\theta JA}$	667	°C/W
Operating Junction Temperature Range	Tj	-40 ~ +125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	$^{\circ}$

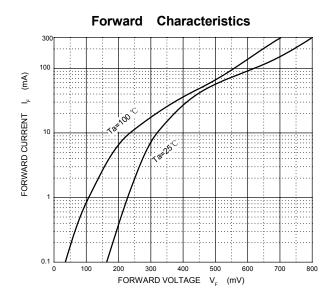
## ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

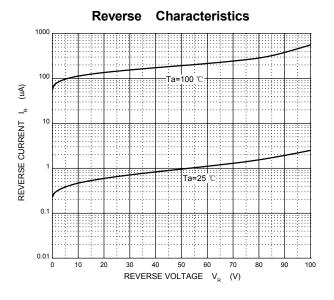
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Reverse breakdown voltage(Note 2)	$V_R$	I <sub>R</sub> = 100μA	100			V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R1</sub> =1.5V			0.3	μΑ
		V <sub>R2</sub> =10V			0.5	
		V <sub>R3</sub> =50V			1	
		V <sub>R4</sub> =75V			2	
Forward voltage(Note 2)	V <sub>F</sub>	I <sub>F1</sub> =0.1mA			0.25	V
		I <sub>F2</sub> =10mA			0.45	
		I <sub>F3</sub> =250mA			1	
Diode capacitance		V <sub>R</sub> =0, f=1MHz		20		_
	C <sub>T</sub>	V <sub>R</sub> =1V, f=1MHz		12		pF

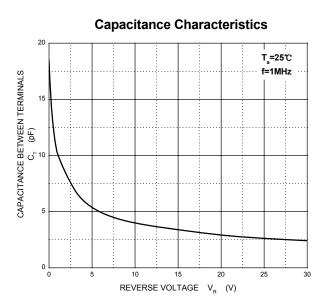
Notes: 1. Part mounted on FR-4 board with recommended pad layout.

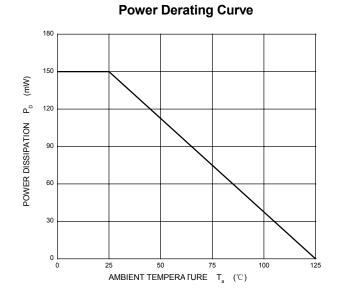
2. Short duration pulse test used to minimize self-heating effect.





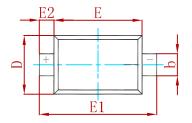


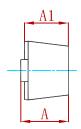


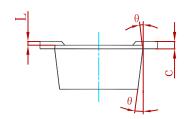




#### **PACKAGE MECHANICAL DATA**

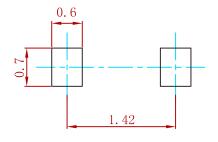






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.510	0.770	0.020	0.031	
A1	0.500	0.700	0.020	0.028	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	0.750	0.850	0.030	0.033	
E	1.100	1.300	0.043	0.051	
E1	1.500	1.700	0.059	0.067	
E2	0.200 REF		0.008 REF		
L	0.010	0.070	0.001	0.003	
θ	7° REF		7° F	REF	

## **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
  3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BAT46X	SOD-523	3000



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